

BRCS080N10SFA

Rev.A Jun.-2024

TO-220F N

N-CHANNEL MOSFET in a TO-220F Plastic Package.

$V_{DS}=100V$ $I_D=68A$

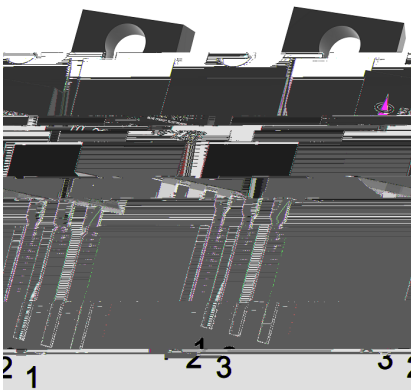
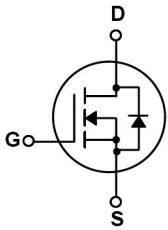
$R_{DS(ON)}@10V$ 8mR(Typ.6.2mR)

$R_{DS(ON)}@4.5V$ 12mR(Typ.8.2mR)

HF Product.

PFC

These devices are well suited for high efficient switched mode power supplies Active power factor correction, electronic lamp ballast based on half bridge topology.



PIN1 G

PIN 2 D

PIN 3 S

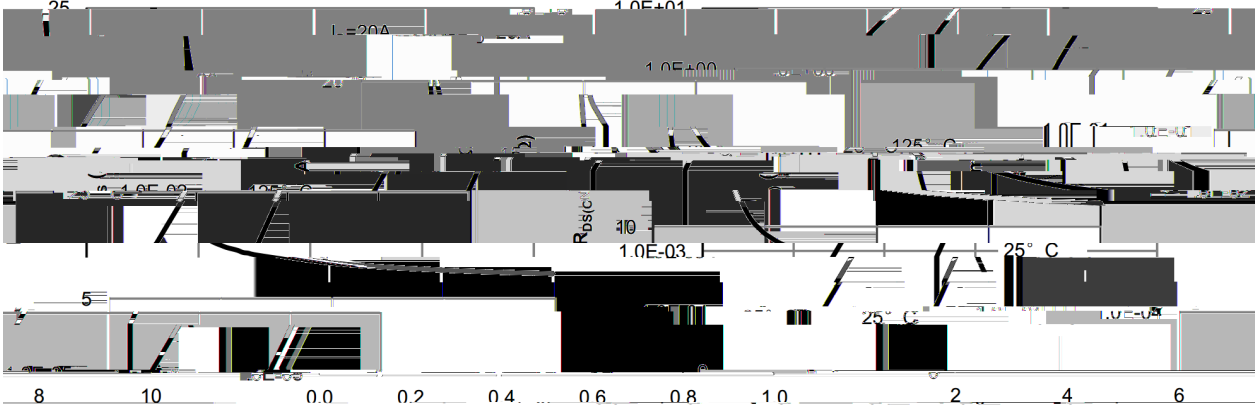
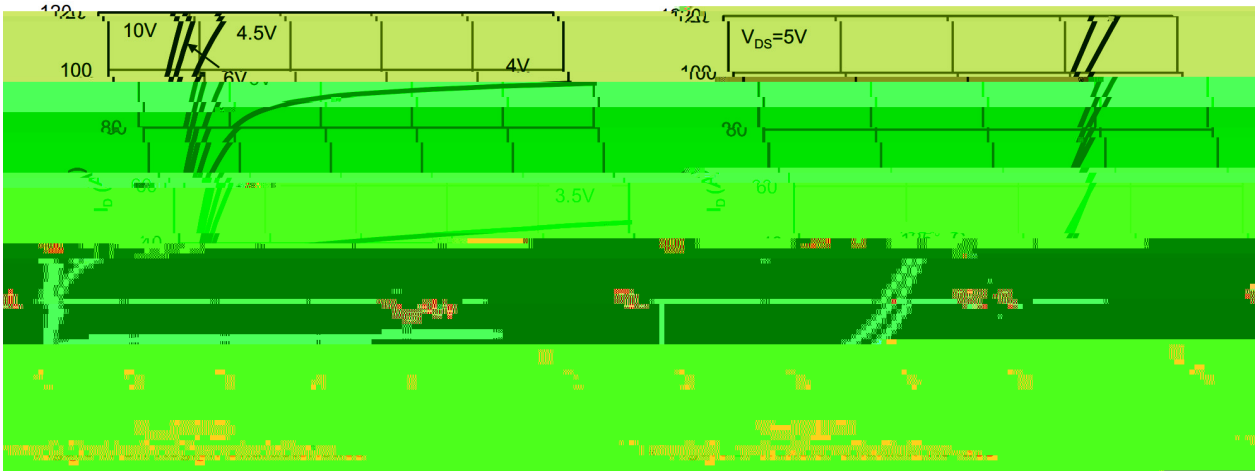
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DATA SHEET

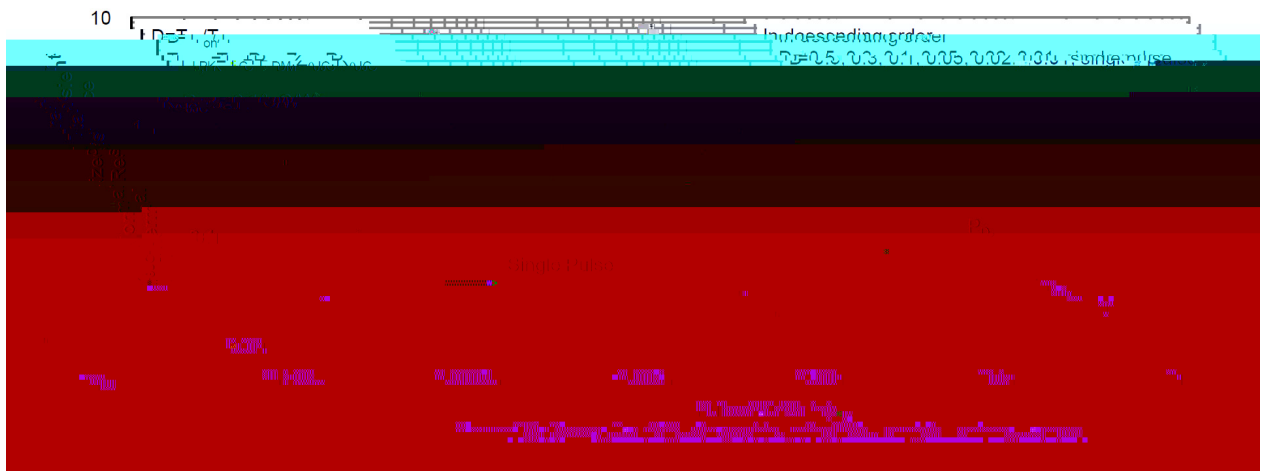
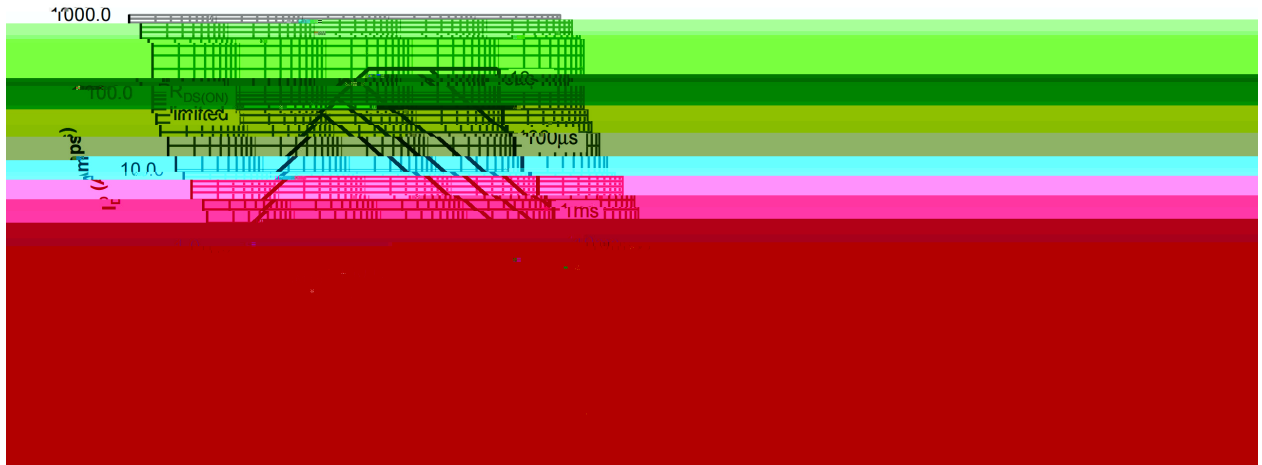
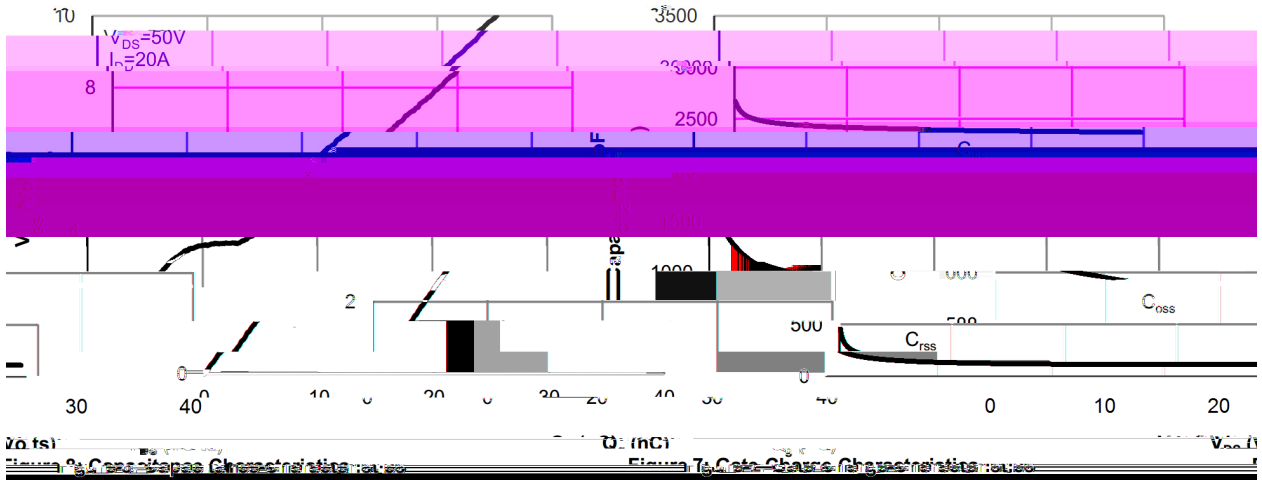
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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/ Electrical Characteristic Curve

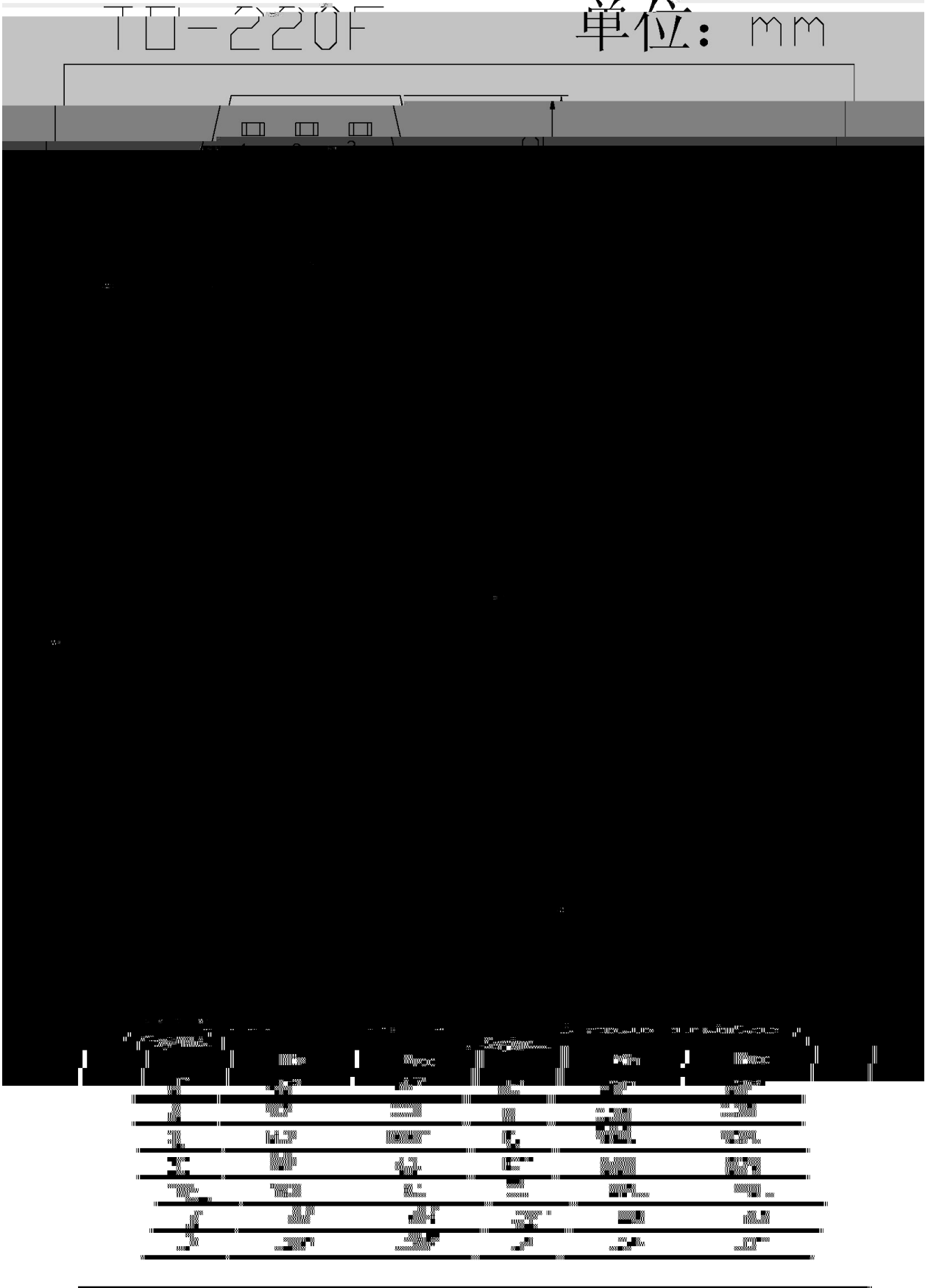


Diode Characteristics Figure 5- Forward Current vs. Forward Voltage Figure 6- Reverse Current vs. Reverse Voltage Figure 7- Dynamic Resistance vs. Forward Current

/ Electrical Characteristic Curve



/ Package Dimensions



() / Temperature Profile for Dip Soldering(Pb-Free)
